

# PJE8402-AU

## 20V N-Channel Enhancement Mode MOSFET – ESD Protected

<b>Voltage</b>	<b>20 V</b>	<b>Current</b>	<b>0.7 A</b>
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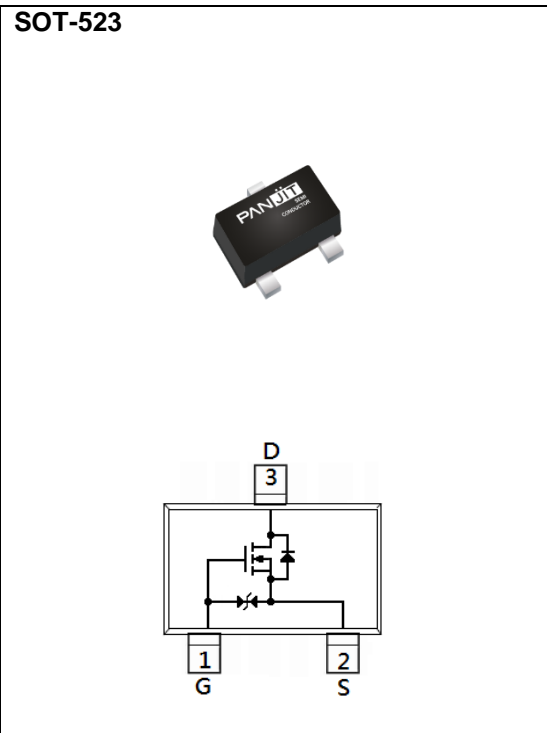
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@0.7A < 150m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@2.5V$ ,  $I_D@0.5A < 220m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@1.8V$ ,  $I_D@0.2A < 400m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- ESD Protected 2KV HBM
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC61249 standard

### Mechanical Data

- Case : SOT-523 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.002 grams

SOT-523



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	$\pm 8$	
Continuous Drain Current <sup>(Note 4)</sup>		$I_D$	0.7	A
Pulsed Drain Current <sup>(Note 1)</sup>		$I_{DM}$	2.8	
Power Dissipation	$T_a=25^\circ\text{C}$	$P_D$	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Thermal Resistance		$R_{\theta JA}$	417	°C/W
- Junction to Ambient <sup>(Note 3,4)</sup>				

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

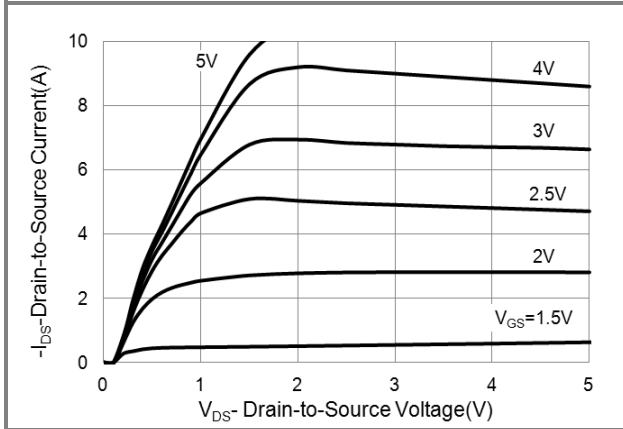
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.78	1	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.7A	-	129	150	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.5A	-	167	220	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.2A	-	260	400	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±10	
<b>Dynamic</b> (Note 5)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.7A, V <sub>GS</sub> =4.5V(Note 1,2)	-	1.6	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.3	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.4	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	-	92	-	pF
Output Capacitance	C <sub>oss</sub>		-	25	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	9	-	
Turn-On Delay Time	t <sub>d(on)</sub>		-	6	-	
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =0.7A, V <sub>GS</sub> =4.5V, R <sub>G</sub> =6Ω(Note 1,2)	-	26	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	41	-	
Turn-Off Fall Time	t <sub>f</sub>		-	31	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>s</sub>	---	-	-	0.4	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>s</sub> =1A, V <sub>GS</sub> =0V	-	0.89	1.2	V

**NOTES :**

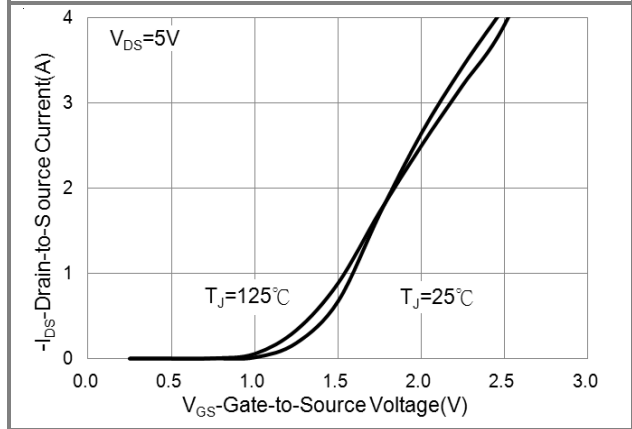
1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.

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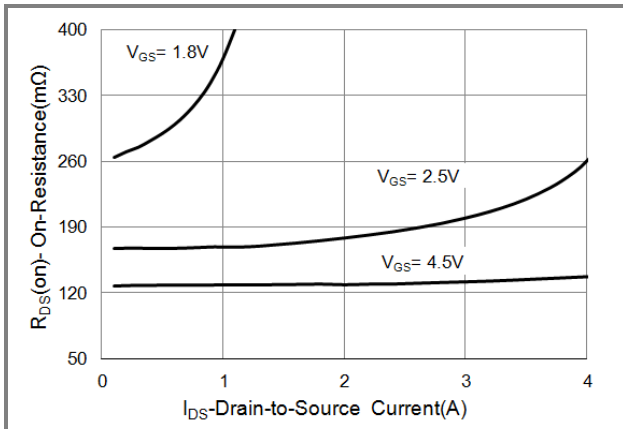
## TYPICAL CHARACTERISTIC CURVES



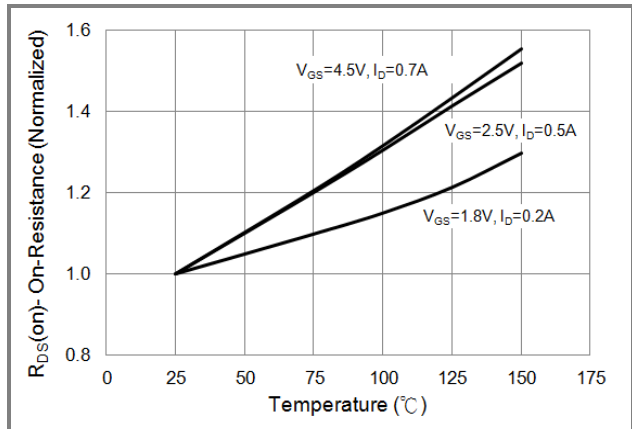
**Fig.1 On-Region Characteristics**



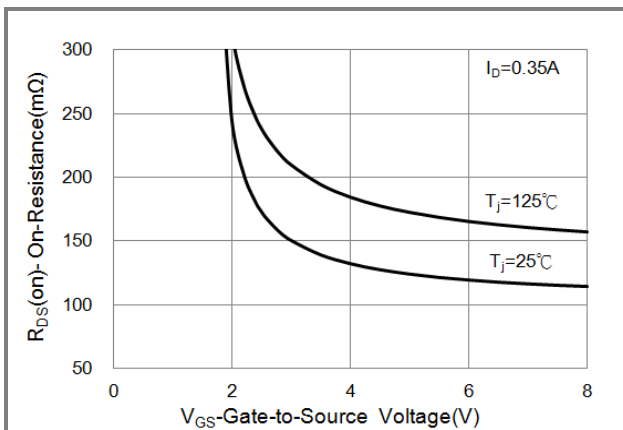
**Fig.2 Transfer Characteristics**



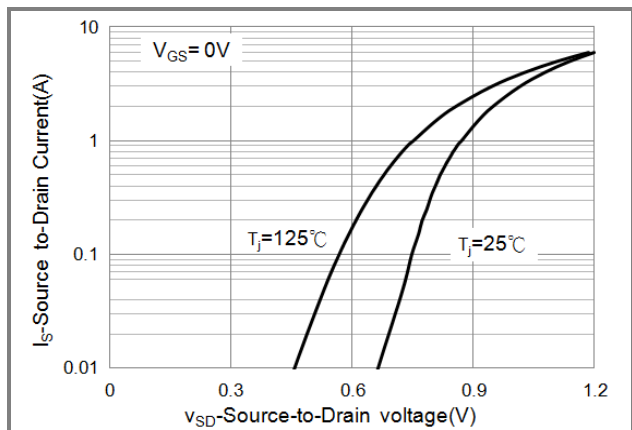
**Fig.3 On-Resistance vs. Drain Current**



**Fig.4 On-Resistance vs. Junction temperature**



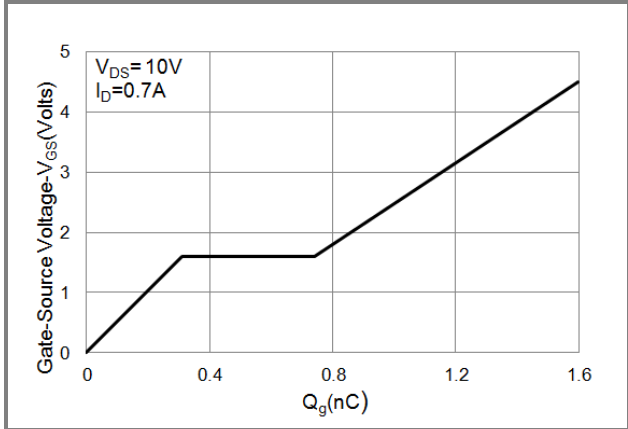
**Fig.5 On-Resistance Variation with  $V_{GS}$**



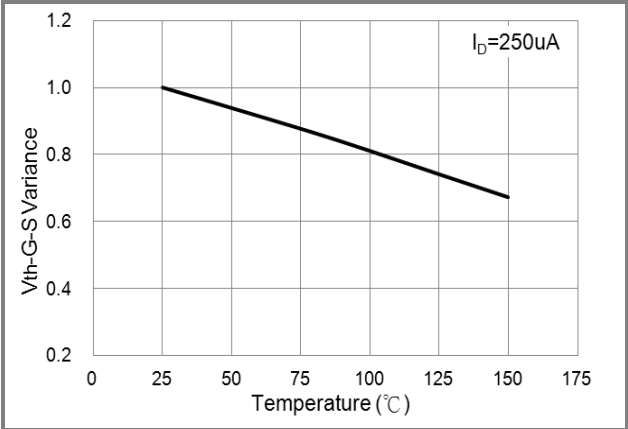
**Fig.6 Body Diode Characteristics**

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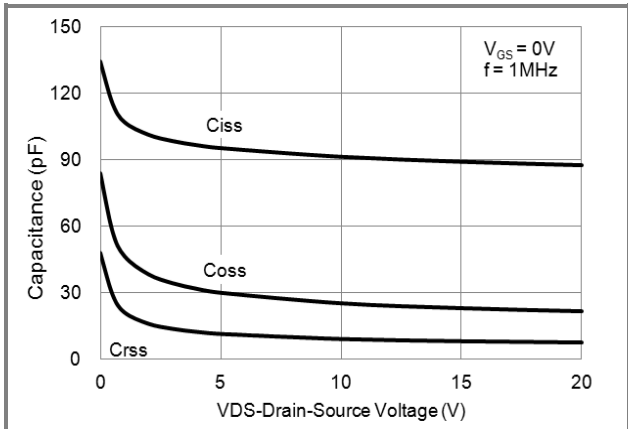
## TYPICAL CHARACTERISTIC CURVES



**Fig.7 Gate-Charge Characteristics**



**Fig.8 Threshold Voltage Variation with Temperature**



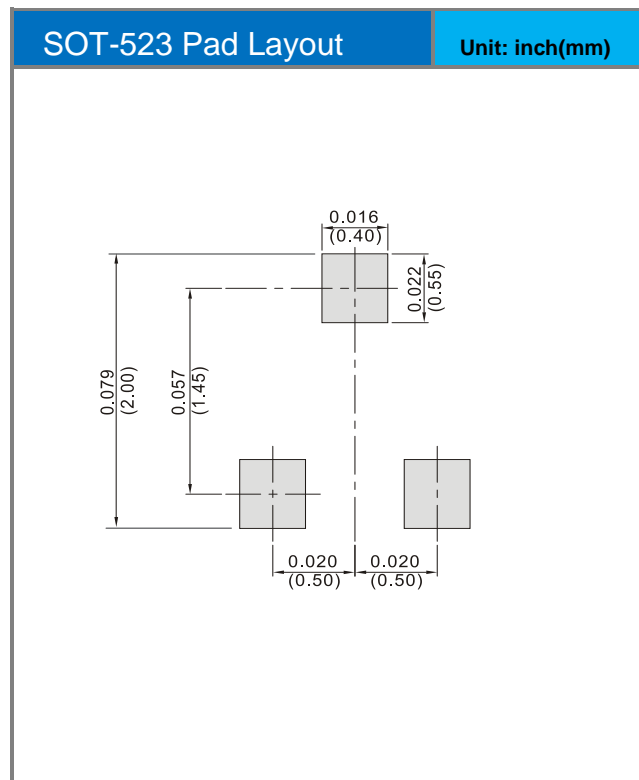
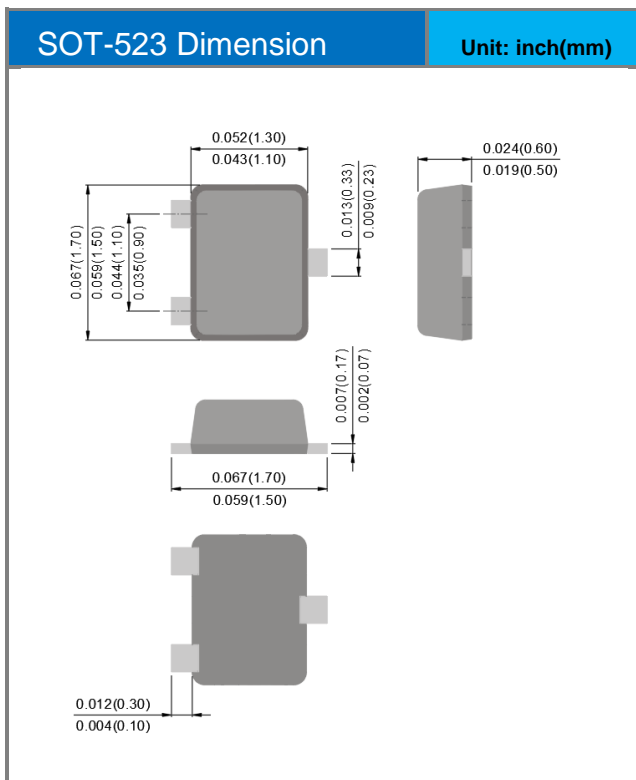
**Fig.9 Capacitance vs. Drain-Source Voltage**

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## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJE8402-AU	SOT-523	4K pcs / 7" reel	E02

## Packaging Information & Mounting Pad Layout



## PJE8402-AU

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